

BUL741

High voltage fast-switching NPN Power Transistor

General features

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- In compliance with the 2002/93/EC European Directive

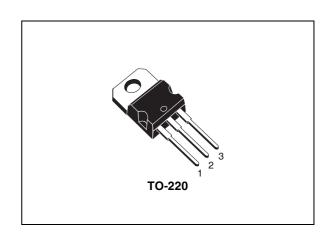
Description

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and high voltage capability.

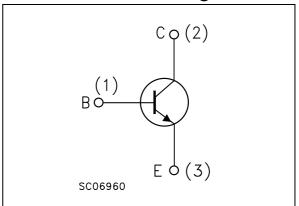
Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.

Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies.



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
BUL741	BUL741	TO-220	Tube

1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	1050	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage ($I_C = 0$, $I_B = 2A$, $t_P < 10ms$)	V _{(BR)EBO}	V
I _C	Collector current	2.5	Α
I _{CM}	Collector peak current (t _P < 5ms)	5	Α
I _B	Base current	1.5	Α
I _{BM}	Base peak current (t _P < 5ms)	3	Α
P _{tot}	Total dissipation at T _c = 25°C	60	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	2.08	°C/W

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 3. Electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} =0V)	V _{CE} =1050V			0.2	10	μА
I _{CEO}	Collector cut-off current (I _B =0)	V _{CE} =400V			10	250	μА
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E =1mA		15	19	24	V
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C =10mA		400	450		V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C =0.7A I _C =2A	$I_B = 0.14A$ $I_B = 0.6A$		0.15 0.5	0.5 1.5	V V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C =2A	I _B =0.6A		1.1	1.5	V
h _{FE}	DC current gain	I _C =0.1A I _C =0.45A	~ —	48 25	70 35	100 50	
t _s	Resistive load Storage time Fall time	$V_{CC} = 125V$ $I_{B1} = -I_{B2} = 0.2A$ $V_{BE(off)} = -5V$	-		2.5 350	3.5 500	μs ns
E _{ar}	Repetitive avalanche energy	L =2mH V _{BE(off)} =-5V	C =1.8nF	5			mJ

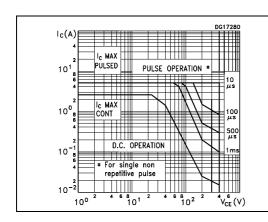
Note (1) Pulsed duration = $300\mu s$, duty cycle $\leq 1.5\%$

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2.1 Typical characteristic

Figure 1. Safe operating area

Figure 2. Derating curve



Ptot (%)

100

80

60

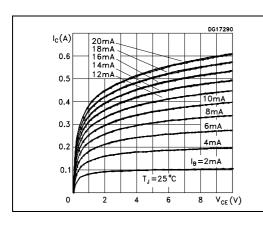
40

20

0 25 50 75 100 125 T_{cose}(°C)

Figure 3. Output characteristics

Figure 4. DC current gain



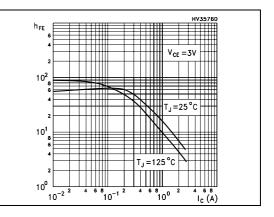
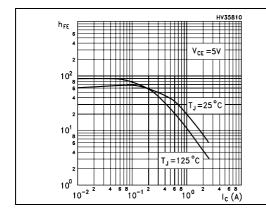


Figure 5. DC current gain

Figure 6. Base-emitter saturation voltage



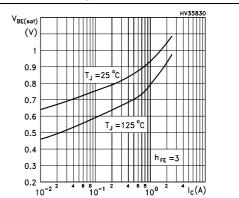
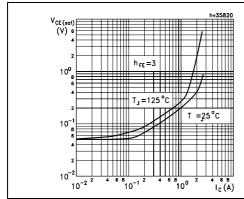


Figure 7. Collector-emitter saturation Figure 8. Resistive load switching on voltage times



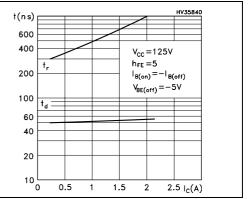
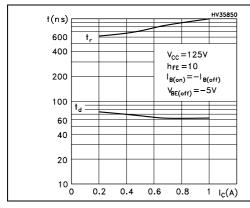


Figure 9. Resistive load switching on times

Figure 10. Resistive load switching off times



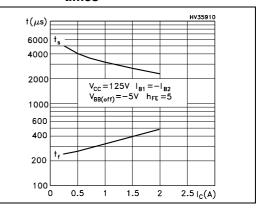
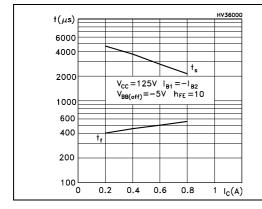
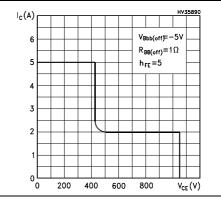


Figure 11. Resistive load switching off times

Figure 12. Reverse biased safe operating area





2.2 Test circuits

Figure 13. Resistive load switching test circuit

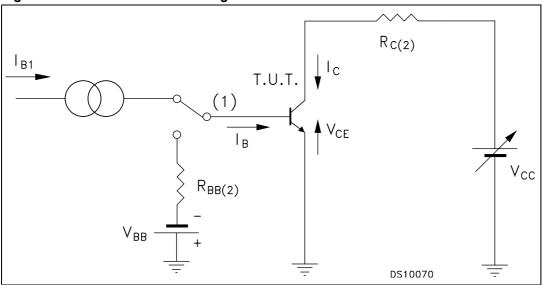
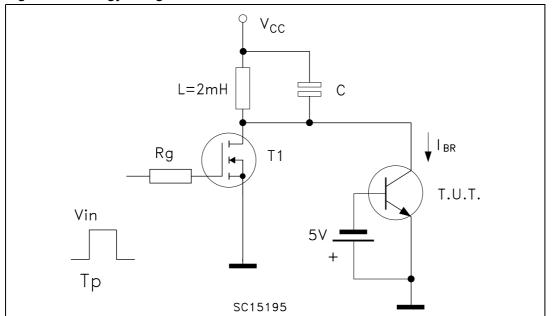


Figure 14. Energy rating test circuit



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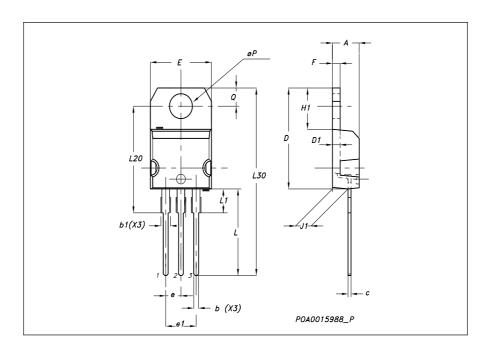
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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TO-220	٨	lechanica	l data

DIM	mm.					
DIM.	MIN.	TYP	MAX.			
A	4.40		4.60			
b	0.61		0.88			
b1	1.14		1.70			
С	0.49		0.70			
D	15.25		15.75			
D1		1.27				
E	10		10.40			
е	2.40		2.70			
e1	4.95		5.15			
F	1.23		1.32			
H1	6.20		6.60			
J1	2.40		2.72			
L	13		14			
L1	3.50		3.93			
L20		16.40				
L30		28.90				
øΡ	3.75		3.85			
Q	2.65		2.95			



4 Revision history

Table 4. Revision history

Date	Revision	Changes
11-Apr-2007	1	Initial release.

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